

	Type	L #	Hits	Search Text	DBs	Time Stamp
1	BRS	L1	1070	257/412	USPAT ; JPO; DERWE NT	2001/10/2 4 16:14
2	BRS	L2	341	(MOS or metal near oxide near transistor) and decoupling near capacitor	USPAT ; JPO; DERWE NT	2001/10/2 4 16:25
3	BRS	L3	0	L2 and (platinum near silicate or PtSi)	USPAT ; JPO; DERWE NT	2001/10/2 4 16:19
4	BRS	L4	2	L2 and (platinum and silicate or PtSi)	USPAT ; JPO; DERWE NT	2001/10/2 4 16:21
5	BRS	L5	810	(platinum near silicate or PtSi)	USPAT ; JPO; DERWE NT	2001/10/2 4 16:21
6	BRS	L6	1	(platinum near silicate or PtSi)and (decoupling near capacitor)	USPAT ; JPO; DERWE NT	2001/10/2 4 16:22
7	BRS	L7	4	(MOS or metal near oxide near transistor) and (decoupling near capacitor) and (flat near band)	USPAT ; JPO; DERWE NT	2001/10/2 4 16:30
8	BRS	L8	0	(MOS or metal near oxide near transistor) and (decoupling near capacitor) and (dopant near level near substrate)	USPAT ; JPO; DERWE NT	2001/10/2 4 16:31

	Type	L #	Hits	Search Text	DBs	Time Stamp
9	BRS	L9	0	(MOS or metal near oxide near transistor) and (decoupling near capacitor) and (modify near dopant near	USPAT ; JPO; DERWE NT	2001/10/24 16:32
10	BRS	L10	0	(MOS or metal near oxide near transistor) and (decoupling near capacitor) and (change near dopant near	USPAT ; JPO; DERWE NT	2001/10/24 16:32
11	BRS	L11	0	(MOS or metal near oxide near transistor) and (decoupling near capacitor) and (dopant near level)	USPAT ; JPO; DERWE NT	2001/10/24 16:32
12	BRS	L12	0	(MOS or metal near oxide near transistor) and (decoupling near capacitor) and (substrate near dopant near level)	USPAT ; JPO; DERWE NT	2001/10/24 16:33
13	BRS	L13	3	(MOS or metal near oxide near transistor) and (decoupling near capacitor) and (substrate near	USPAT ; JPO; DERWE NT	2001/10/24 16:34
14	BRS	L14	5	(MOS or metal near oxide near transistor) and (decoupling near capacitor) and (dopant near concentration)	USPAT ; JPO; DERWE NT	2001/10/24 16:40
15	BRS	L15	5	(MOS or metal near oxide near transistor) and (decoupling near capacitor) and (substrate) and (dopant near	USPAT ; JPO; DERWE NT	2001/10/24 16:40
16	BRS	L16	0	(MOS or metal near oxide near transistor) and (decoupling near capacitor) and (substrate) near (dopant near	USPAT ; JPO; DERWE NT	2001/10/24 16:41

	Type	L #	Hits	Search Text	DBs	Time Stamp
17	BRS	L17	0	(decoupling near capacitor) and (substrate)near (dopant near concentration)	USPAT; JPO; DERWE NT	2001/10/24 16:41
18	BRS	L18	0	(decoupling near capacitor) and (dopant near concentration near substrate)	USPAT; JPO; DERWE NT	2001/10/24 16:41
19	BRS	L19	6	(decoupling near capacitor) and (dopant near concentration)	USPAT; JPO; DERWE NT	2001/10/24 17:03
20	BRS	L20	80234	Chen CY.in.	USPAT; JPO; DERWE NT	2001/10/24 17:04
21	BRS	L21	10	DHAKA.in.	USPAT; JPO; DERWE NT	2001/10/24 17:06
22	BRS	L22	9	"3619735"	USPAT; JPO; DERWE NT	2001/10/24 17:08
23	BRS	L23	19	"3769105"	USPAT; JPO; DERWE NT	2001/10/24 17:12
24	BRS	L24	44	"4437139"	USPAT; JPO; DERWE NT	2001/10/24 17:22